

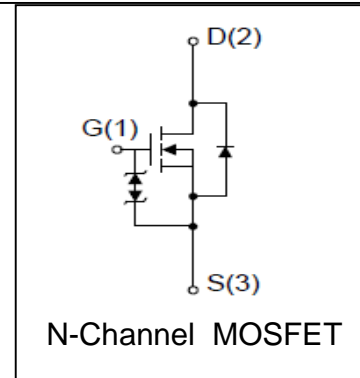
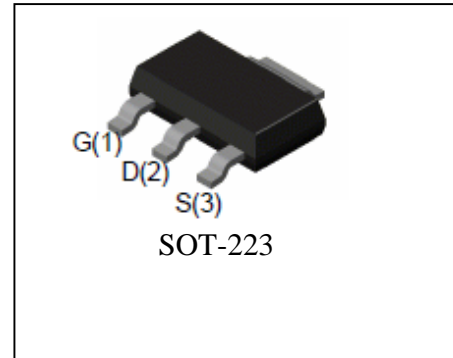
Features

- 100V/3A,
 $R_{DS(ON)} = 130m\Omega$ (Type) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 140m\Omega$ (Type) @ $V_{GS} = 4.5V$
- ESD Protected
- Reliable and Rugged
- Ultra Low On-Resistance
- 100% avalanche tested
- Lead Free and Green Available

Applications

- Power Management

Pin Description



Absolute Maximum Ratings

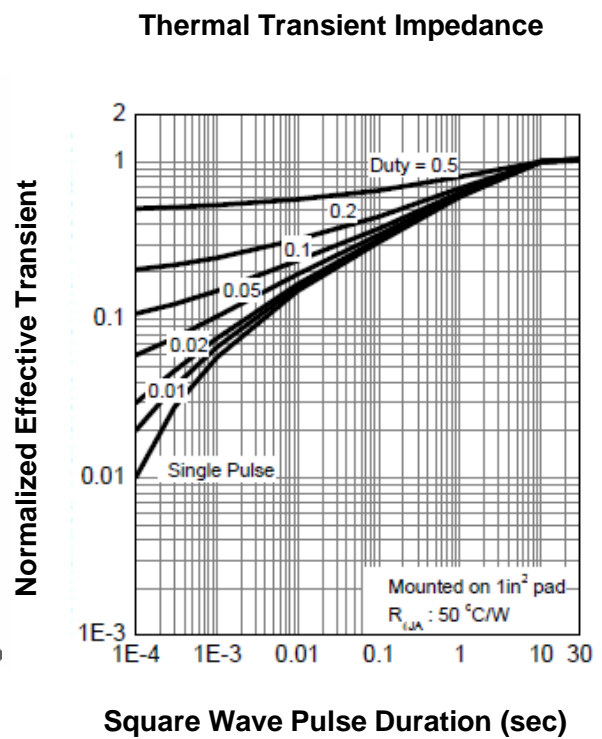
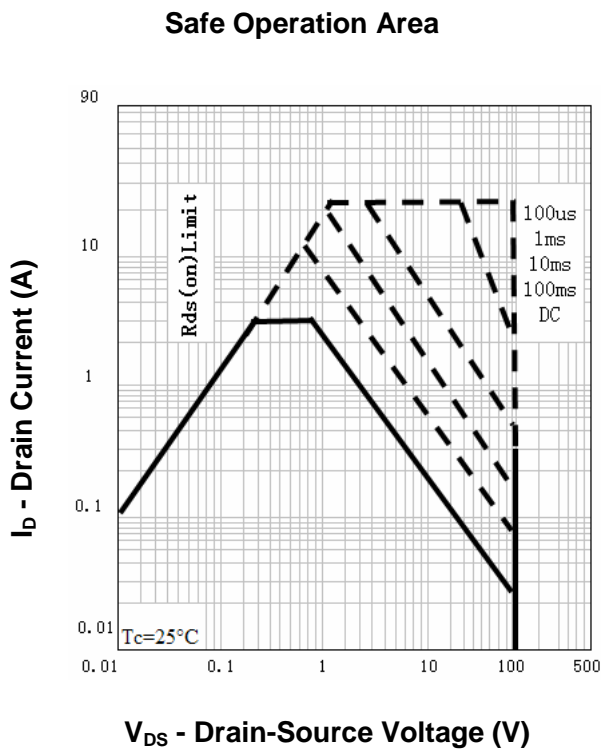
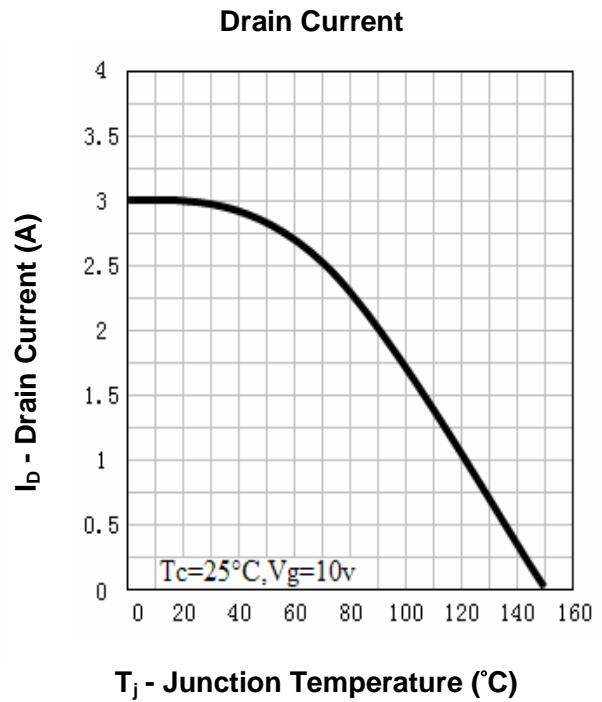
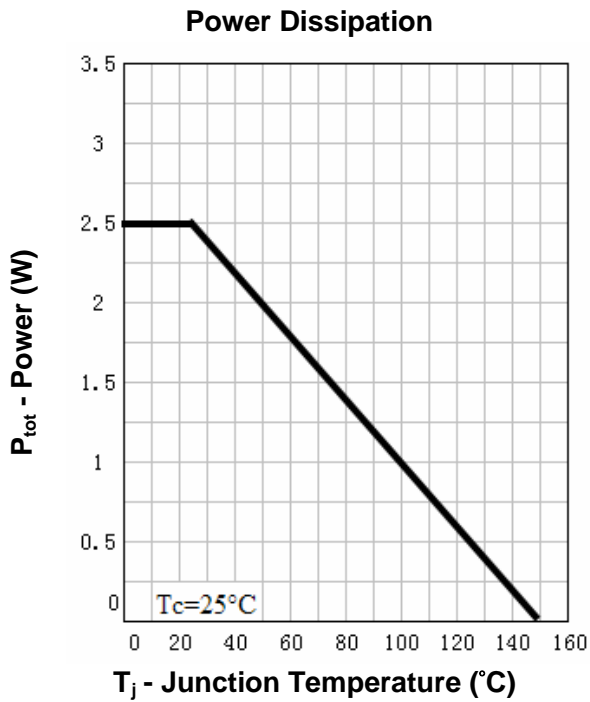
Symbol	Parameter	Rating	Unit
Common Ratings ($T_A = 25^\circ C$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	± 20	
T_J	Maximum Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
I_S	Diode Continuous Forward Current	$T_C = 25^\circ C$ 3	A
Mounted on Large Heat Sink			
I_{DP}	300 μs Pulse Drain Current Tested	$T_C = 25^\circ C$ 12	A
I_D	Continuous Drain Current	$T_C = 25^\circ C$ 3 ^①	A
		$T_C = 70^\circ C$ 2.5	
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$ 2.5	W
		$T_C = 70^\circ C$ 1.6	
$R_{\theta JA}$ ^②	Thermal Resistance-Junction to Ambient	50	$^\circ C/W$

Electrical Characteristics ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU1HE3D			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	100			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V$			1	μA
		$T_J=85^\circ C$			30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	1.5	2	2.7	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 16V, V_{DS}=0V$			± 10	μA
$R_{DS(ON)}^{(3)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=3A$		130	145	$m\Omega$
		$V_{GS}=4.5V, I_{DS}=2A$		140	180	$m\Omega$
Diode Characteristics						
$V_{SD}^{(3)}$	Diode Forward Voltage	$I_{SD}=2.5A, V_{GS}=0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=2.5A, di_{SD}/dt=100A/\mu s$		43		ns
Q_{rr}	Reverse Recovery Charge			78		nC
Dynamic Characteristics ⁽⁴⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1MHz$		0.6		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=30V,$ Frequency=1.0MHz		930		pF
C_{oss}	Output Capacitance			85		
C_{riss}	Reverse Transfer Capacitance			45		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=50V, R_L=30\Omega,$ $I_{DS}=3A, V_{GEN}=10V,$ $R_G=25\Omega$		13		ns
t_r	Turn-on Rise Time			15		
$t_{d(OFF)}$	Turn-off Delay Time			29		
t_f	Turn-off Fall Time			16		
Gate Charge Characteristics ⁽⁴⁾						
Q_g	Total Gate Charge	$V_{DS}=50V, V_{GS}=10V,$ $I_{DS}=3A$		20	26	nC
Q_{gs}	Gate-Source Charge			5		
Q_{gd}	Gate-Drain Charge			5.9		

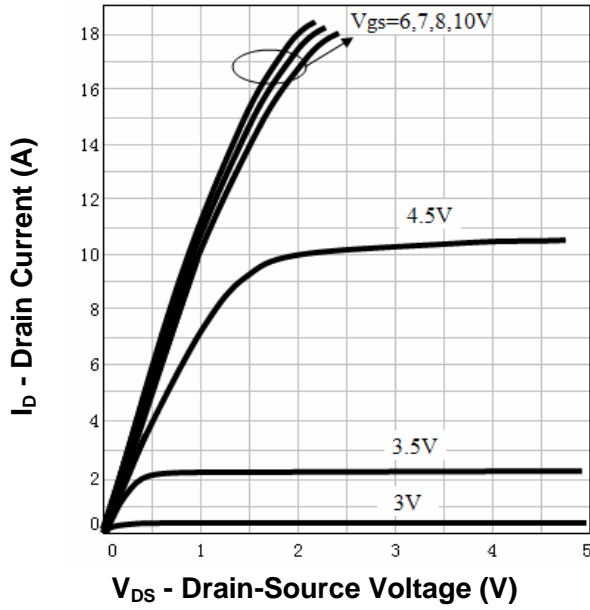
- Notes:
- ① Current limited by maximum junction temperature.
 - ② When mounted on 1 inch square copper board, $t \leq 10\text{sec}$.
 - ③ Pulse test ; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ④ Guaranteed by design, not subject to production testing.

Typical Characteristics

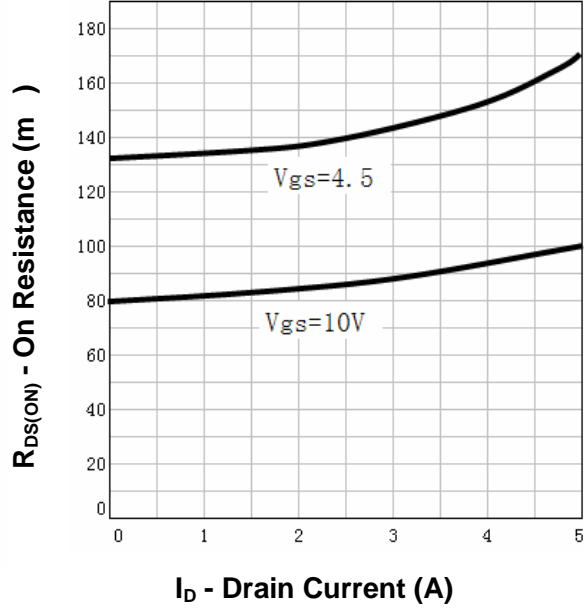


Typical Characteristics

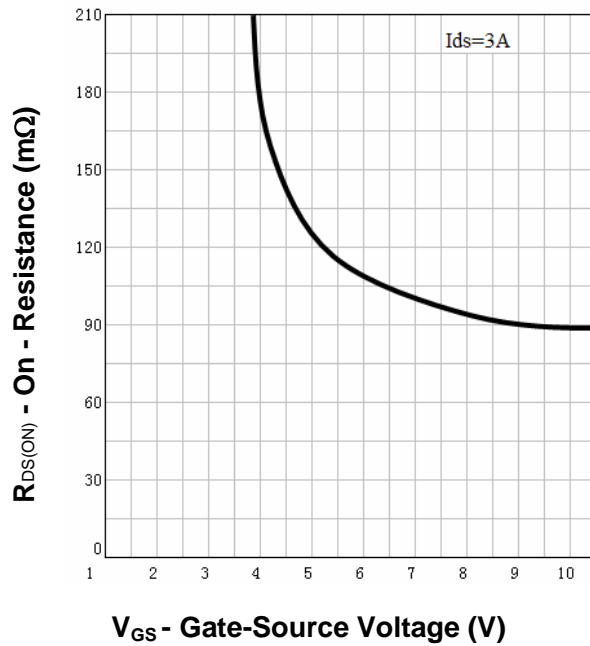
Output Characteristics



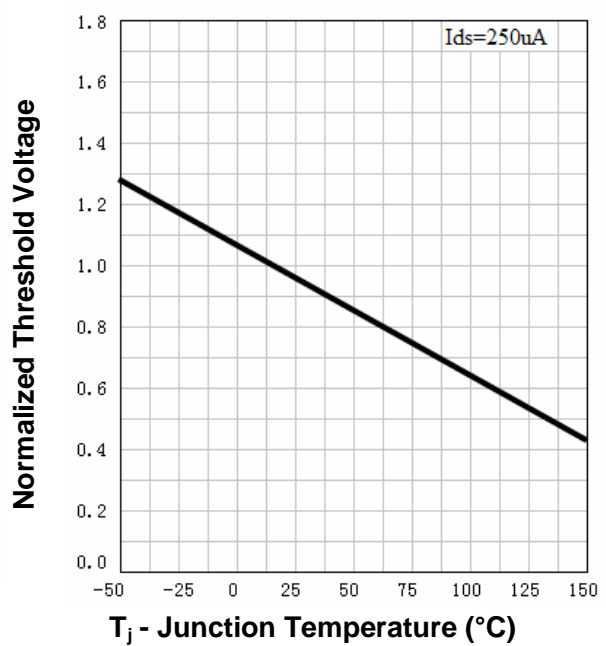
Drain-Source On Resistance



Drain-Source On Resistance

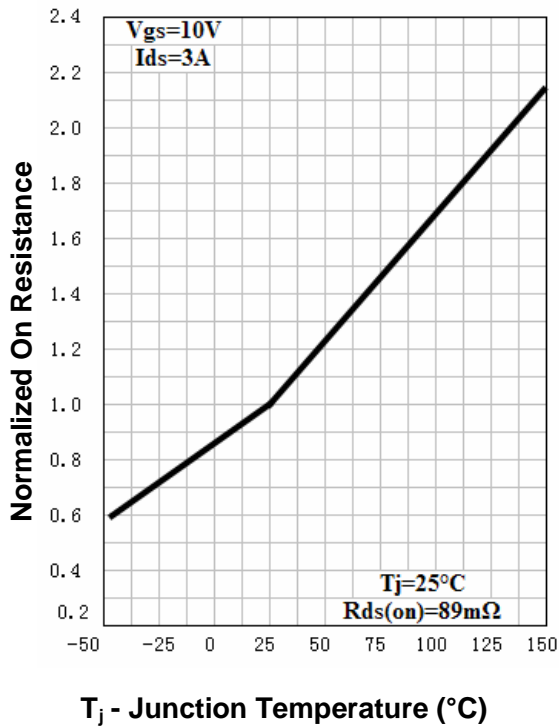


Gate Threshold Voltage

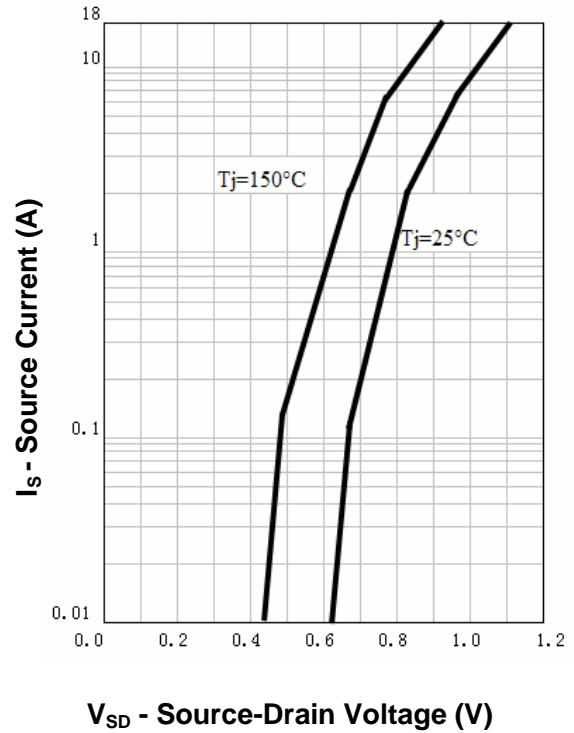


Typical Characteristics

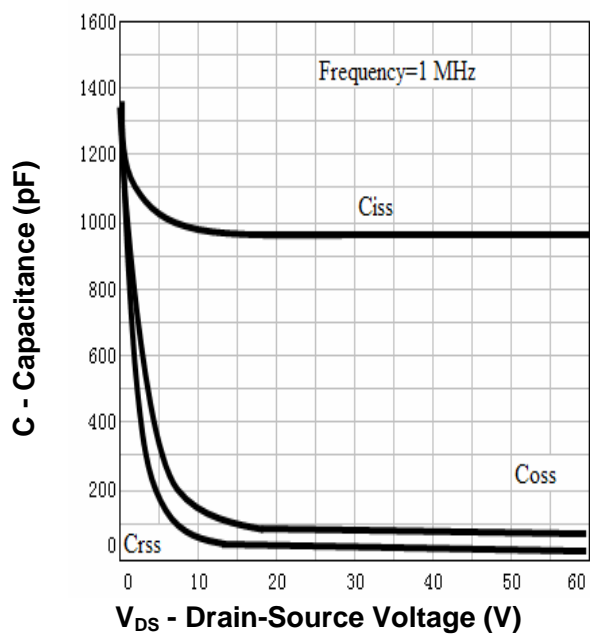
Drain-Source On Resistance



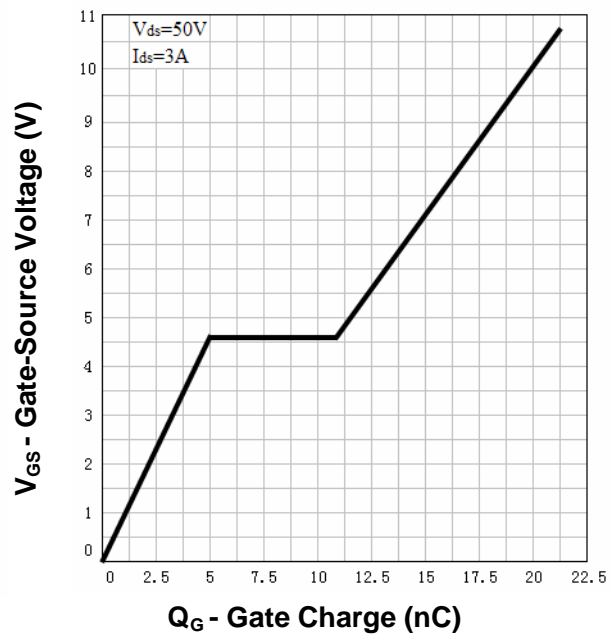
Source-Drain Diode Forward



Capacitance



Gate Charge



Ordering and Marking Information**RU1HE3****Package (Available)**

D : SOT-223; H: SOP-8 ;

Operating Temperature Range

C : -55 to 150 °C

Assembly Material

G : Green & Lead Free

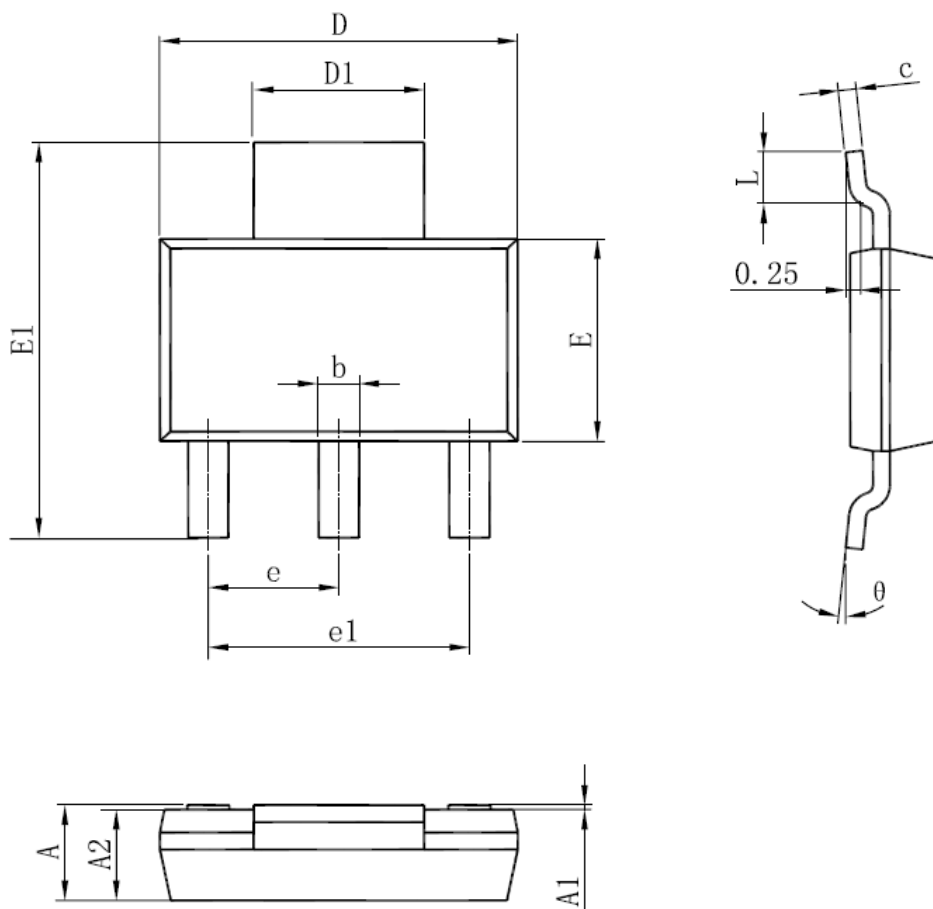
Packaging

T : TUBE

TR : Tape & Reel

Package Information

SOT-223



SYMBOL	MM		INCH		SYMBOL	MM		INCH	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	1.520	1.800	0.060	0.071	E	3.300	3.700	0.130	0.146
A1	0.000	0.100	0.000	0.004	E1	6.830	7.070	0.269	0.278
A2	1.500	1.700	0.059	0.067	e	2.300(BSC)		0.091(BSC)	
b	0.660	0.820	0.026	0.032	e1	4.500	4.700	0.177	0.185
c	0.250	0.350	0.010	0.014	L	0.900	1.150	0.035	0.045
D	6.200	6.400	0.244	0.252	θ	0°	10°	0°	10°
D1	2.900	3.100	0.114	0.122					

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

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